



# 제25회 한국반도체학술대회

The 25<sup>th</sup> Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 7일(수), 16:15-17:30

Room F (봉래, 6층)

## F. Silicon and Group-IV Devices and Integration Technology 분과

### [WF4-F] Steep-Slope II : NC-FET

좌장: 김경록 교수(UNIST), 김상완 교수(아주대학교)

WF4-F-1 16:15-16:30	<b>Use of Negative Capacitance to Lower the Switching Voltage of Nanoelectromechanical Relay</b> Kihun Choe, Wonseok Lee, and Changhwan Shin <i>Department of Electrical and Computer Engineering, University of Seoul</i>
WF4-F-2 16:30-16:45	<b>Impact of Ferroelectric Capacitor's Electrode Area on the Performance of Negative (Differential) Capacitance Field Effect Transistor</b> Hyungki Cho, Jaemin Shin, and Changhwan Shin <i>Department of Electrical and Computer Engineering, University of Seoul</i>
WF4-F-3 16:45-17:00	<b>Tunnel Field Effect Transistor with Ferroelectric Gate Dielectric</b> Kitae Lee <sup>1</sup> , Junil Lee <sup>1</sup> , Ryoongbin Lee <sup>1</sup> , Euyhwan Park <sup>1</sup> , Sihyun Kim <sup>1</sup> , Hyun-Min Kim <sup>1</sup> , Sangwan Kim <sup>2</sup> , and Byung-Gook Park <sup>1</sup> <i><sup>1</sup>Department of Electrical and Computer Engineering, Seoul National University, <sup>2</sup>Department of Electrical and Computer Engineering, Ajou University</i>
WF4-F-4 17:00-17:15	<b>Transient Response of Polarization Switching in PZT Ferroelectric Capacitor</b> Hansol Ku and Changhwan Shin <i>Department of Electrical and Computer Engineering, University of Seoul</i>